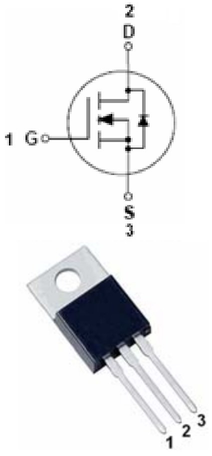
50A,60V N-Channel Power Mosfet

BL50N60

FEATURES

- $R_{DS(ON)}$ =17mΩ@ V_{GS} = 10V,I_D=20A
- High Current Capacity : I_D=50A
- Low reverse current.

Lead-free



TO-220AB

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

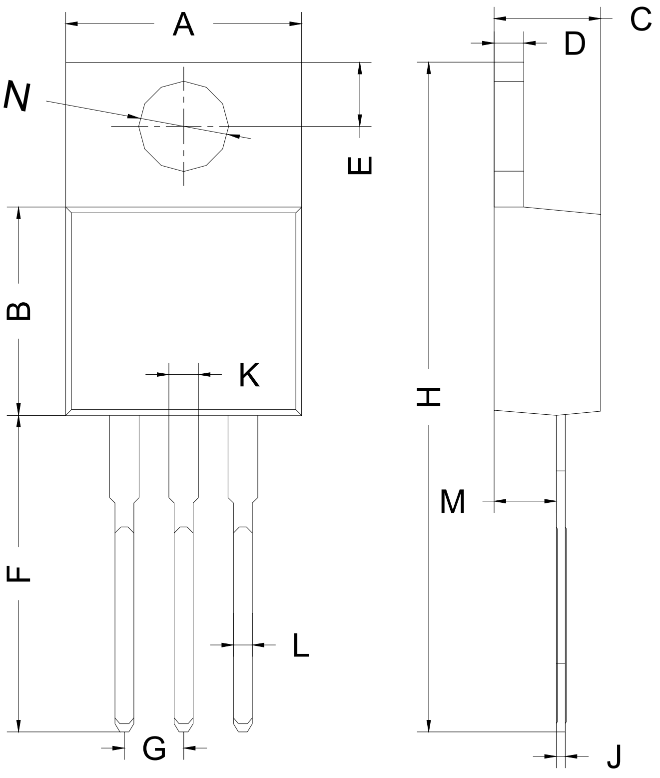
Symbol	**Parameter**	**Value**	**Units**
V_{DSS}	Drain-Source voltage	60	V
V_{GSS}	Gate -Source voltage	±20	V
I_D	Continuous Drain Current	50	A
P_D	Power Dissipation	2	W
T_J	Junction Temperature	150	℃
T_{OPR}, Tstg	Operating and Storage Temperature	-55 to +150	℃

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	**Symbol**	**Test conditions**	**MIN**	**TYP**	**MAX**	**UNIT**
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA	60	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.2	2.0	3.0	V
Static drain-Source on-resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=20A	-	17	20	mΩ

PACKAGE OUTLINE

Plastic surface mounted package TO-220AB



TO-220AB		
Dim	Min	Max
A	9.80	10.30
B	8.70	9.10
C	4.57 Typical	
D	1.27 Typical	
E	2.64	2.84
F	13.14	13.74
G	2.44	2.64
H	28.03	28.83
J	0.38 Typical	
K	1.22	1.32
L	0.71	0.91
M	2.50 Typical	
N	3.86 Typical	
All Dimensions in mm		